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Features

- GaN on SiC D-Mode Transistor Technology
- Common-Source Configuration
- Unmatched, Coupled DC and RF
- Ideal for Pulsed and CW Applications up to 50 V
- 50 V Typical Bias, Class AB
- Excellent Thermal Resistance
- Thermally-Enhanced Plastic SOT-89 Package
- MTTF = 600 years ($T_J < 200^\circ\text{C}$)
- Halogen-Free “Green” Mold Compound
- RoHS* Compliant and 260°C Reflow Compatible
- MSL1

Description

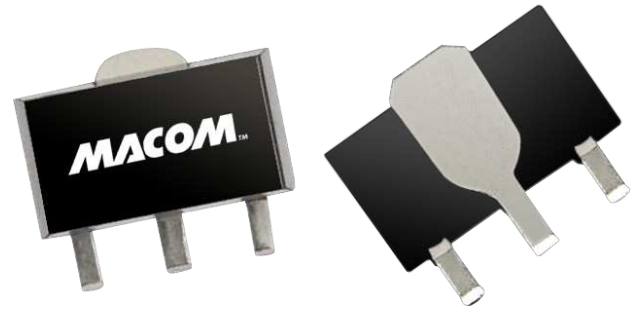
The MAGX-000040-00500P is a GaN on SiC unmatched power device offering the widest RF frequency capability, most reliable high voltage operation, lowest overall transistor size, cost and weight in a “TRUE SMT”™ plastic package.

Use of an internal stress buffer technology allows reliable operation at junction temperatures up to 200°C . The small package size and excellent RF performance make it an ideal replacement for costly flanged or metal-backed module components.

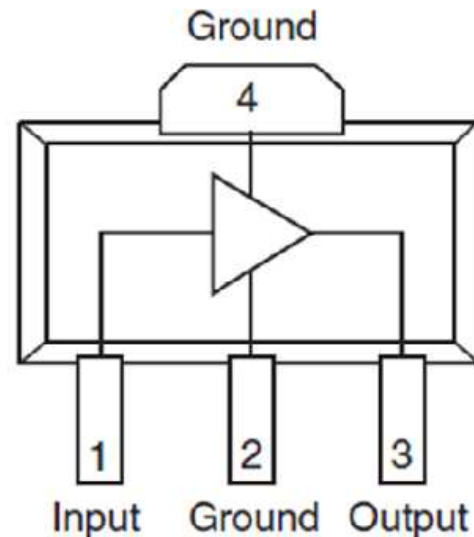
Ordering Information¹

| Part Number | Package |
|--------------------|----------------|
| MAGX-000040-00500P | Bulk Packaging |
| MAGX-000040-0050TP | 500 Piece Reel |
| MAGX-000040-SB2PPR | Sample Board |

1. Reference Application Note M513 for reel size information.



Functional Schematic



Pin Configuration

| Pin No. | Function |
|---------|-------------------|
| 1 | V_{GG}/RF_{IN} |
| 2 | GND |
| 3 | V_{DD}/RF_{OUT} |
| 4 | GND |

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

GaN Wideband 5 W CW / Pulsed Transistor in Plastic Package DC - 4.0 GHz

Rev. V2

Typical Narrowband RF Performance²: $V_{DD} = 50\text{ V}$, $I_{DQ} = 17\text{ mA}$, $T_A = 25^\circ\text{C}$

| Parameter | 1 GHz | 1.6 GHz | 3.0 GHz | 3.5 GHz | Units |
|---------------------------------|-------|---------|---------|---------|-------|
| Linear Gain | 18 | 17 | 14 | 13.5 | dB |
| Pulsed Peak Output Power (P3dB) | 5.3 | 5.3 | 5.3 | 5.3 | W |
| Pulsed Power Gain (P3dB) | 15 | 14 | 11 | 10.5 | dB |
| Drain Efficiency (P3dB) | 61 | 55 | 53 | 50 | % |

2. Device optimally matched in narrowband load-pull test system.

Electrical Specifications³: Freq. = 1.6 GHz, $V_{DD} = 50\text{ V}$, $I_{DQ} = 17\text{ mA}$, $T_A = 25^\circ\text{C}$, $Z_0 = 50\ \Omega$

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Units |
|--|-------------------------------|-----------|------|------|------|-------|
| RF FUNCTIONAL TESTS: Pulse Width = 1 ms, 10% Duty Cycle | | | | | | |
| Pulsed Peak Output Power | $P_{IN} = 0.28\text{ W Peak}$ | P_{OUT} | 4.5 | 5.3 | - | Wpk |
| Pulsed Power Gain | $P_{IN} = 0.28\text{ W Peak}$ | G_P | 12 | 13 | - | dB |
| Pulsed Drain Efficiency | $P_{IN} = 0.28\text{ W Peak}$ | η_D | 47 | 51.3 | - | % |
| Load Mismatch Stability | $P_{IN} = 0.28\text{ W Peak}$ | VSWR-S | - | 5:1 | - | - |
| Load Mismatch Tolerance | $P_{IN} = 0.28\text{ W Peak}$ | VSWR-T | - | 10:1 | - | - |
| RF FUNCTIONAL TESTS: CW | | | | | | |
| CW Output Power | P3dB | P_{OUT} | - | 4 | - | W |

3. Device measured in MACOM 1.4-1.6 GHz evaluation board. See tuning information on page 4.

Electrical Characteristics: $T_A = 25^\circ\text{C}$

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Units |
|--------------------------------|--|--------------|------|------|------|---------------|
| DC CHARACTERISTICS | | | | | | |
| Drain-Source Leakage Current | $V_{GS} = -8\text{ V}$, $V_{DS} = 175\text{ V}$ | I_{DS} | - | - | 200 | μA |
| Gate Threshold Voltage | $V_{DS} = 5\text{ V}$, $I_D = 0.6\text{ mA}$ | $V_{GS(TH)}$ | -5 | -3 | -2 | V |
| Forward Transconductance | $V_{DS} = 5\text{ V}$, $I_D = 1500\text{ mA}$ | G_M | 0.1 | - | - | S |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | $V_{DS} = 0\text{ V}$, $V_{GS} = -8\text{ V}$, $F = 1\text{ MHz}$ | C_{ISS} | - | 0.5 | - | pF |
| Output Capacitance | $V_{DS} = 50\text{ V}$, $V_{GS} = -8\text{ V}$, $F = 1\text{ MHz}$ | C_{OSS} | - | 0.18 | - | pF |
| Reverse Transfer Capacitance | $V_{DS} = 50\text{ V}$, $V_{GS} = -8\text{ V}$, $F = 1\text{ MHz}$ | C_{RSS} | - | 0.05 | - | pF |

2

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Absolute Maximum Ratings ^{4,5,6,7,8}

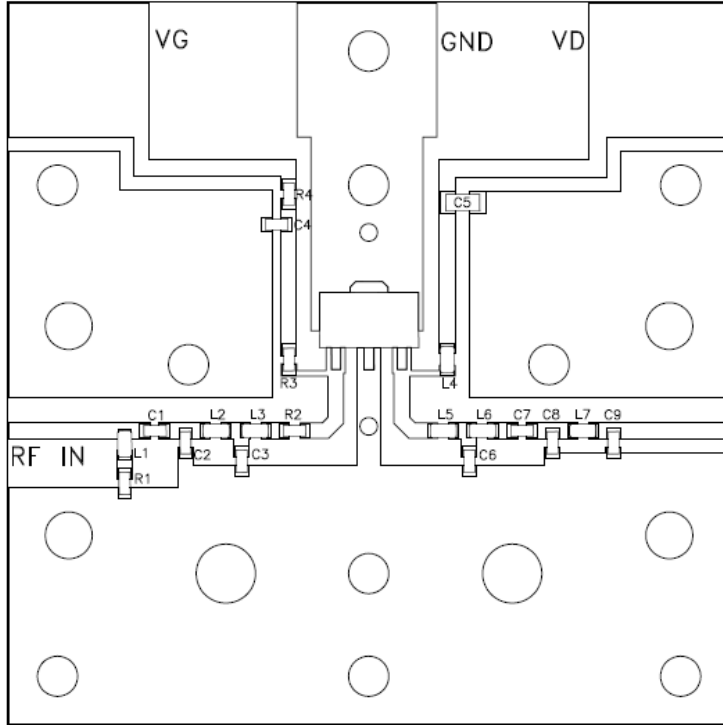
| Parameter | Absolute Max. |
|---------------------------------------|-----------------|
| Input Power | 30 dBm |
| Drain Supply Voltage, V_{DD} | +65 V |
| Gate Supply Voltage, V_{GG} | -8 V to 0 V |
| Supply Current, I_{DD} | 300 mA |
| Power Dissipation, CW (85°C) | 12 W |
| Power Dissipation, Pulsed Mode (85°C) | 31 W |
| Junction Temperature ⁷ | 200°C |
| Operating Temperature | -40°C to +95°C |
| Storage Temperature | -65°C to +150°C |

4. Exceeding any one or combination of these limits may cause permanent damage to this device.
5. MACOM does not recommend sustained operation near these survivability limits.
6. For saturated performance it is recommended that the sum of $(3 * V_{DD} + \text{abs}(V_{GG})) \leq 175 \text{ V}$.
7. Operating at nominal conditions with $T_J \leq 200^\circ\text{C}$ will ensure $\text{MTTF} > 1 \times 10^6$ hours. Junction temperature directly affects device MTTF and should be kept as low as possible to maximize lifetime.
8. Junction Temperature (T_J) = $T_C + \Theta_{JC} * ((V * I) - (P_{OUT} - P_{IN}))$.

Typical CW thermal resistance (Θ_{JC}) = 11.1°C/W.

Typical transient thermal resistance (Θ_{JC}) = $\Theta_{JC} = 4.0^\circ\text{C/W}$ (1 ms pulse, 10% duty cycle).

L-Band Evaluation Board Details and Recommended Tuning Solutions



Parts measured on evaluation board (12-mil thick RO4003C). Electrical and thermal ground is provided using a copper-filled, via-hole array (not pictured), and evaluation board is mounted to a metal plate.

Matching is provided using lumped elements. Recommended tuning solutions for 2 frequency ranges are detailed in the parts list below.

Bias Sequencing

Turning the device ON

1. Set V_G to the pinch-off value (V_P), typically -5 V.
2. Turn on V_D to nominal voltage (50 V).
3. Increase V_{GS} to desired quiescent current.
4. Apply RF power to desired level.

Turning the device OFF

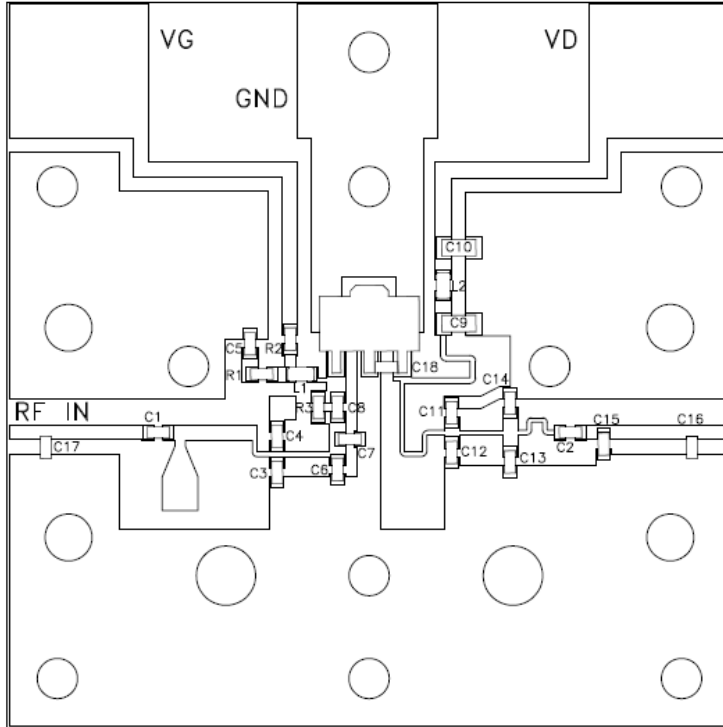
1. Turn the RF power off.
2. Decrease V_G down to V_P .
3. Turn off V_D .
4. Turn off V_G .

Parts List

| Part | Frequency = 1.0 - 1.2 GHz | Frequency = 1.4 - 1.6 GHz |
|------|--|---------------------------------|
| C1 | 10 pF, 600L, ATC | 10 pF, 600L, ATC |
| C2 | 3.9 pF 0.5 pF, 600L, ATC ⁹ | 2.4 pF, 600L, ATC |
| C3 | 6.8 pF 1 pF, 600L, ATC ⁹ | 5.6 pF, 600L, ATC |
| C4 | 10 nF, 0402, Murata | 10 nF, 0402, Murata |
| C5 | 10 nF, 0603, Murata | 10 nF, 0603, Murata |
| C6 | 3.3 pF, 600L, ATC | 2.4 pF, 600L, ATC |
| C7 | 10 pF, 600L, ATC | 10 pF, 600L, ATC |
| C8 | 1.3 pF, 600L, ATC | 1.3 pF, 600L, ATC |
| C9 | 2 pF, 600L, ATC | 1.6 pF, 600L, ATC |
| L1 | 27 nH, 0402HP, Coilcraft | 27 nH, 0402HP, Coilcraft |
| L2 | 4.3 nH, 0402HP, Coilcraft | 3.3 nH, 0402HP, Coilcraft |
| L3 | 3.3 nH, 0402HP, Coilcraft | 1 nH, 0402HP, Coilcraft |
| L4 | 30 nH, 0402HP, Coilcraft | 12 nH, 0402HP, Coilcraft |
| L5 | 16 nH, 0402HP, Coilcraft | 8.2 nH, 0402HP, Coilcraft |
| L6 | 8.2 nH, 0402HP, Coilcraft | 3.9 nH, 0402HP, Coilcraft |
| L7 | 2.7 nH, 0402HP, Coilcraft | 3.3 nH, 0402HP, Coilcraft |
| R1 | 49.9 Ω , 0402, Panasonic | 49.9 Ω , 0402, Panasonic |
| R2 | 5.1 Ω , 0402, Panasonic | 5.1 Ω , 0402, Panasonic |
| R3 | 200 Ω , 0402, Panasonic | 200 Ω , 0402, Panasonic |
| R4 | 1 k Ω , 0402, Panasonic | 1 k Ω , 0402, Panasonic |

9. Parallel combination of two capacitors.

S-Band Evaluation Board Details and Recommended Tuning Solutions



Parts measured on evaluation board (12-mil thick RO4003C). Electrical and thermal ground is provided using a copper-filled, via-hole array (not pictured), and evaluation board is mounted to a metal plate.

Matching is provided using lumped elements. Recommended tuning solution for the 2.9-3.3 GHz frequency band is detailed in the parts list below.

Bias Sequencing

Turning the device ON

1. Set V_G to the pinch-off value (V_P), typically -5 V.
2. Turn on V_D to nominal voltage (50 V).
3. Increase V_{GS} to desired quiescent current.
4. Apply RF power to desired level.

Turning the device OFF

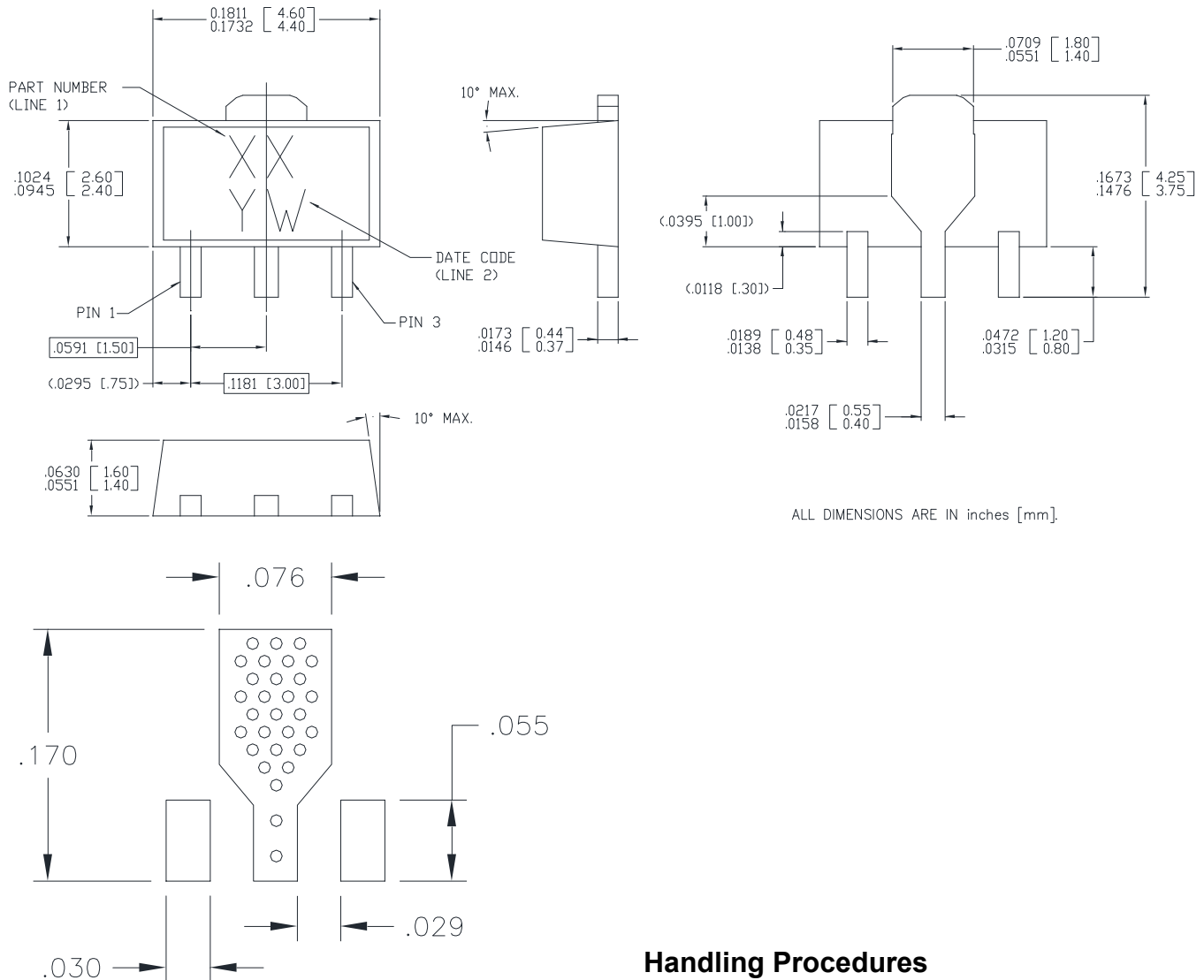
1. Turn the RF power off.
2. Decrease V_G down to V_P .
3. Turn off V_D .
4. Turn off V_G .

Parts List, 2.9 - 3.3 GHz

| Part | Description |
|------|--|
| C1 | 5.6 pF, 600L, ATC |
| C2 | 5.6 pF, 600L, ATC |
| C3 | 1 pF 0.02 pF, 600L, ATC ¹⁰ |
| C4 | 1 pF, 600L, ATC |
| C5 | 10 nF, 0402, Murata |
| C6 | 0.8 pF, 600L, ATC |
| C7 | 1.5 pF, 600L, ATC |
| C8 | 2.4 pF, 600L, ATC |
| C9 | 1 nF, 0603, Murata |
| C10 | 10 nF, 0603, Murata |
| C11 | 1.1 pF, 600L, ATC |
| C12 | 1.5 pF, 600L, ATC |
| C13 | 1.6 pF, 600L, ATC |
| C14 | 1.3 pF, 600L, ATC |
| C15 | 0.6 pF, 600L, ATC |
| C16 | 0.2 pF, 600L, ATC |
| C17 | 0.6 pF, 600L, ATC |
| C18 | 0.3 pF, 600L, ATC |
| L1 | 56 nH, 0402HP, Coilcraft |
| L2 | 12 nH, 0402HP, Coilcraft |
| R1 | 100 Ω , 0402, Panasonic |
| R2 | 1.2 k Ω , 0402, Panasonic |
| R3 | 100 Ω , 0402, Panasonic |

10. Parallel combination of two capacitors.

SOT-89 Package Outline and Landing Pattern^{11,12}



Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

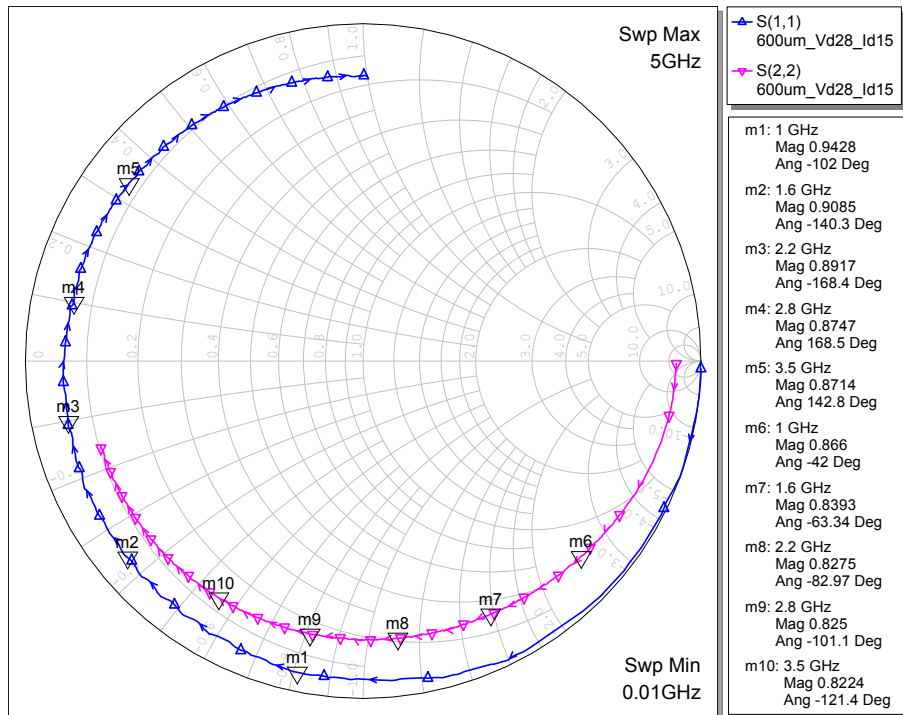
Gallium Nitride Devices and Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these Class 1A devices.

11. Reference Application Note M538 for lead-free solder reflow recommendations. Meets JEDEC moisture sensitivity level 1 requirements. Lead plating is 100% Sn matte.
12. Landing pattern indicates dimensions of solder mask opening. Cu-filled via holes under the ground are typically used for optimal thermal performance. Recommended pattern: 8 mil diameter, 8 mil spacing.

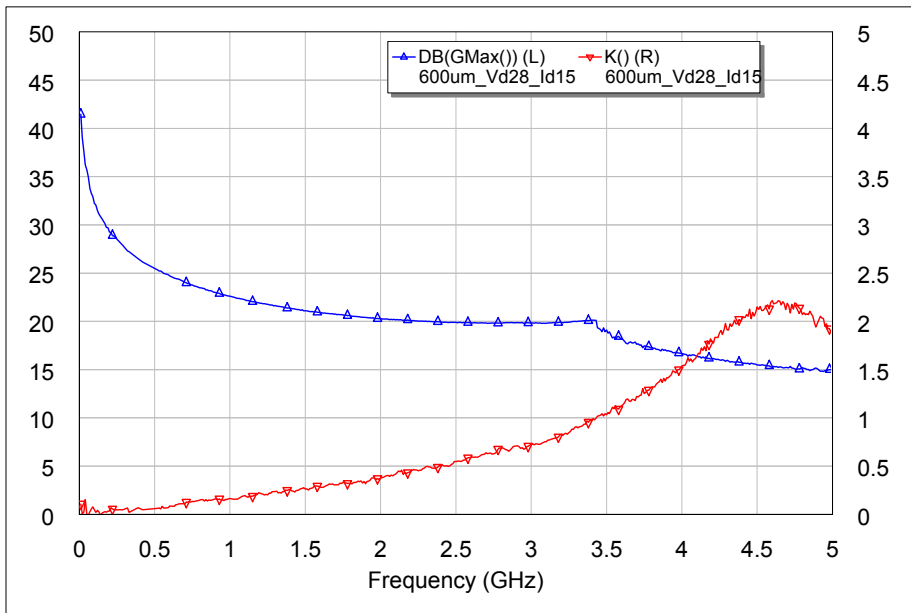
Applications Section

S-Parameter Data: $T_A = 25^\circ\text{C}$, $V_{DD} = 28\text{ V}$, $I_{DQ} = 15\text{ mA}$

Device S11 and S22



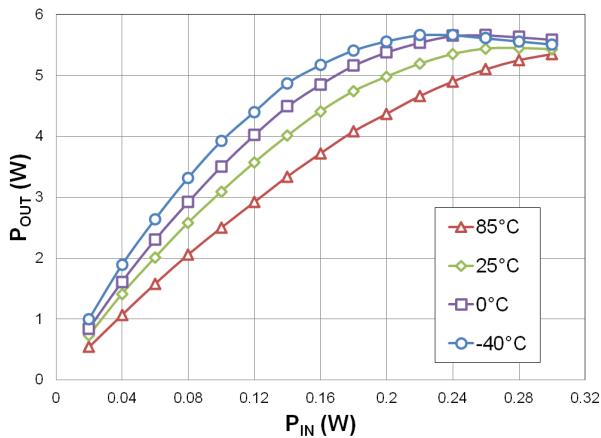
Gmax and K-Factor vs Frequency



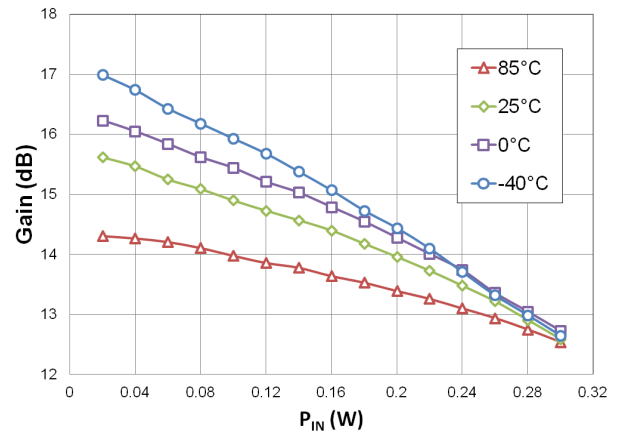
Applications Section

Typical Performance Curves (reference 1.4-1.6 GHz parts list):
1.6 GHz, 1 ms Pulse, 10% Duty Cycle, $V_{DD} = 50\text{ V}$, $T_A = 25^\circ\text{C}$, $Z_0 = 50\ \Omega$

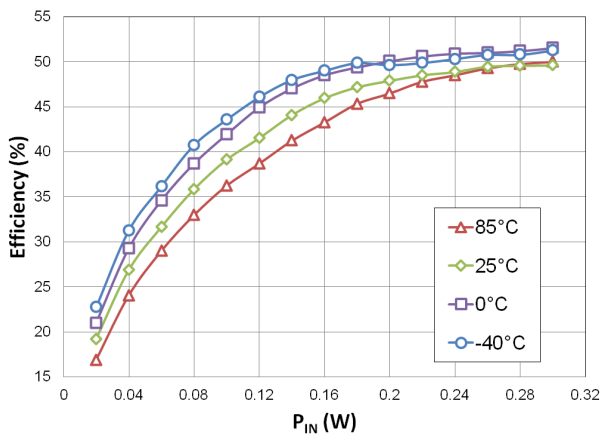
Output Power vs. Input Power



Gain vs. Input Power



Drain Efficiency vs. Input Power

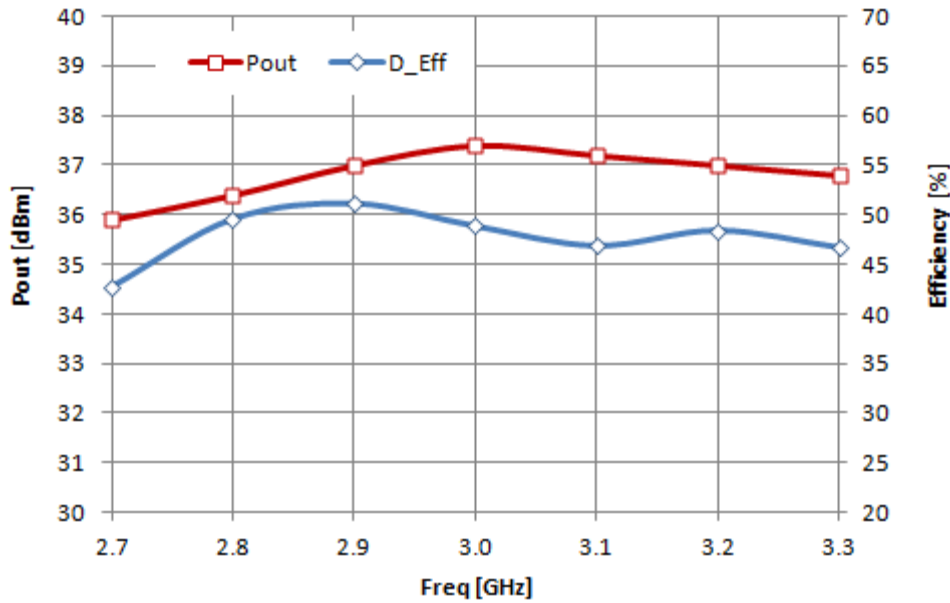


Applications Section

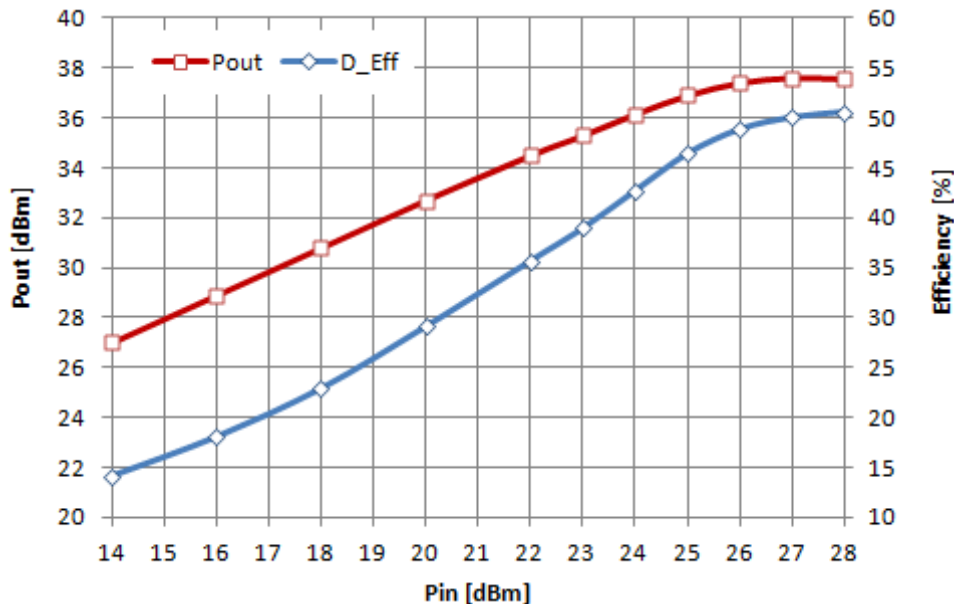
Typical Performance Curves (reference 2.9-3.3 GHz parts list):

300 μ s Pulse, 10% Duty Cycle, $V_{DD} = 50$ V, $T_A = 25^\circ\text{C}$, $Z_0 = 50 \Omega$

Output Power and Efficiency vs. Frequency ($P_{IN} = 26$ dBm)



Output Power and Efficiency vs. Input Power (Frequency = 3.0 GHz)

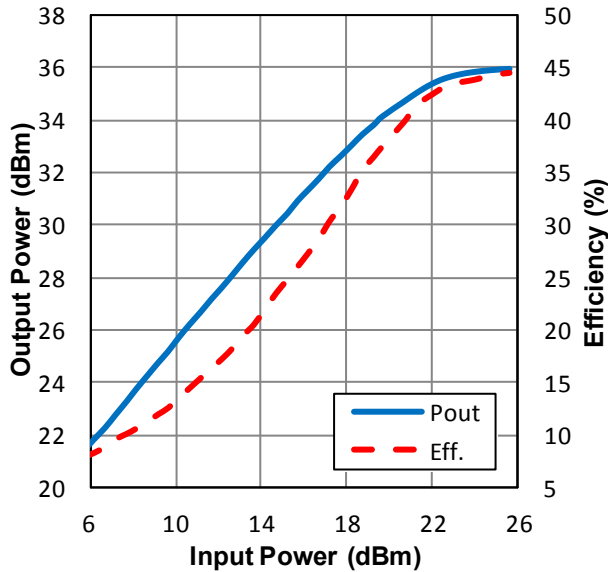


Applications Section

Typical CW Performance:

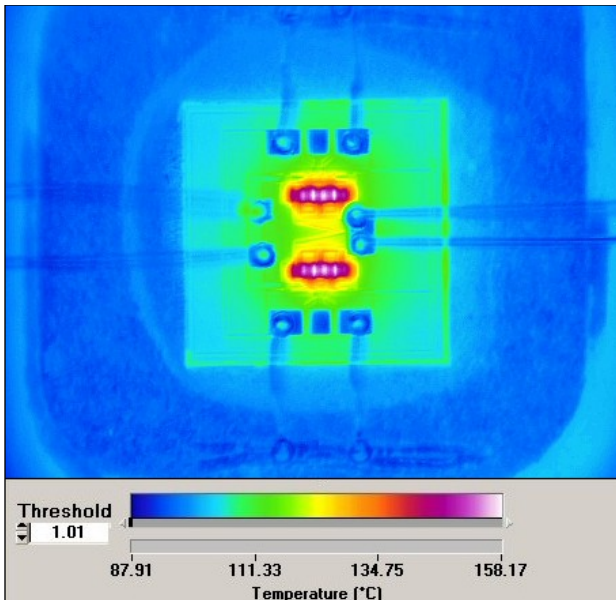
Freq. = 2.7 GHz, $V_{DD} = 50$ V, $T_A = 25^\circ\text{C}$, $I_{DQ} = 13$ mA, Load-Pull Test Fixture

Output Power and Efficiency vs. Input Power



Typical CW Thermal Performance: $V_{DD} = 50$ V, $T_A = 85^\circ\text{C}$, $I_{DQ} = 13$ mA

Thermal Image



| P_{IN} (W) | P_{OUT} (W) | Eff. (%) | T_J ($^\circ\text{C}$) | P_{DISS} (W) | R_{TH} ($^\circ\text{C}/\text{W}$) |
|-----------------|------------------|-------------|-------------------------------|-------------------|---|
| 0.18 | 4.47 | 41.2 | 158 | 6.56 | 11.1 |